



2811
#12/C
Amend C
y/Robinson
8/29/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Application of :
Jun OSANAI et al. :
Serial No. 09/944,365 : Group Art Unit - 2811
Filed: August 31, 2001 : Examiner - Thien F. Tran
For: COMPLEMENTARY MOS :
SEMICONDUCTOR DEVICE AND :
METHOD OF MANUFACTURING :
THE SAME : Docket No. S004-4393

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MS FEE AMENDMENT
COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL RESPONSE

S I R:

In further response to the Office Action mailed
March 3, 2003, applicants further amend their application as
follows:

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 91, line 3,
with the following rewritten paragraph:

--The formation of the P+resistor 116 and the
N+resistor 117 is attained by simultaneously doping the

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360.00 DP

MAILING CERTIFICATE ON
LAST PAGE

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